

Kazumasa Hiramatsu

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#	Paper	IF	Citations
179	P-Type Conduction in Mg-Doped GaN Treated with Low-Energy Electron Beam Irradiation (LEEBI). <i>Japanese Journal of Applied Physics</i> , 1989 , 28, L2112-L2114	1.4	1549
178	Effects of an buffer layer on crystallographic structure and on electrical and optical properties of GaN and Ga _{1-x} Al _x N (0 <i>Journal of Crystal Growth</i> , 1989 , 98, 209-219	1.6	623
177	Fabrication and characterization of low defect density GaN using facet-controlled epitaxial lateral overgrowth (FACELO). <i>Journal of Crystal Growth</i> , 2000 , 221, 316-326	1.6	364
176	Selective growth of wurtzite GaN and Al _x Ga _{1-x} N on GaN/sapphire substrates by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1994 , 144, 133-140	1.6	278
175	Relaxation Process of the Thermal Strain in the GaN/Al ₂ O ₃ Heterostructure and Determination of the Intrinsic Lattice Constants of GaN Free from the Strain. <i>Japanese Journal of Applied Physics</i> , 1992 , 31, L1454-L1456	1.4	236
174	Photoluminescence of Mg-doped p-type GaN and electroluminescence of GaN p-n junction LED. <i>Journal of Luminescence</i> , 1991 , 48-49, 666-670	3.8	226
173	Effects of the buffer layer in metalorganic vapour phase epitaxy of GaN on sapphire substrate. <i>Thin Solid Films</i> , 1988 , 163, 415-420	2.2	226
172	Growth and Luminescence Properties of Mg-Doped GaN Prepared by MOVPE. <i>Journal of the Electrochemical Society</i> , 1990 , 137, 1639-1641	3.9	193
171	Relaxation Mechanism of Thermal Stresses in the Heterostructure of GaN Grown on Sapphire by Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 1528-1533	1.4	190
170	Growth of single crystalline GaN film on Si substrate using 3C-SiC as an intermediate layer. <i>Journal of Crystal Growth</i> , 1991 , 115, 634-638	1.6	173
169	Preparation of high-quality AlN on sapphire by high-temperature face-to-face annealing. <i>Journal of Crystal Growth</i> , 2016 , 456, 155-159	1.6	165
168	Fabrication of GaN Hexagonal Pyramids on Dot-Patterned GaN/Sapphire Substrates via Selective Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1995 , 34, L1184-L1186	1.4	161
167	Growth of single crystal GaN substrate using hydride vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1990 , 99, 381-384	1.6	160
166	Heteroepitaxial Growth and the Effect of Strain on the Luminescent Properties of GaN Films on (111 $\bar{2}$ 0) and (0001) Sapphire Substrates. <i>Japanese Journal of Applied Physics</i> , 1988 , 27, L1384-L1386	1.4	148
165	Annealing of an AlN buffer layer in N ₂ O for growth of a high-quality AlN film on sapphire. <i>Applied Physics Express</i> , 2016 , 9, 025501	2.4	139
164	Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L1000-L1002	1.4	88
163	Electron beam effects on blue luminescence of zinc-doped GaN. <i>Journal of Luminescence</i> , 1988 , 40-41, 121-122	3.8	80

162	Epitaxial lateral overgrowth techniques used in group III nitride epitaxy. <i>Journal of Physics Condensed Matter</i> , 2001 , 13, 6961-6975	1.8	79
161	Preparation of Al _x Ga _{1-x} N/GaN heterostructure by MOVPE. <i>Journal of Crystal Growth</i> , 1990 , 104, 533-538.	6	79
160	Defect structure in selective area growth GaN pyramid on (111)Si substrate. <i>Applied Physics Letters</i> , 2000 , 76, 2701-2703	3.4	75
159	Sharp band edge photoluminescence of high-purity CuInS ₂ single crystals. <i>Applied Physics Letters</i> , 2001 , 78, 742-744	3.4	74
158	Growth of Si-doped Al _x Ga _{1-x} N on (0001) sapphire substrate by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1991 , 115, 648-651	1.6	66
157	Selective Area Growth of GaN on Si Substrate Using SiO ₂ Mask by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, L966-L969	1.4	61
156	Optical and Crystalline Properties of Epitaxial-Lateral-Overgrown-GaN Using Tungsten Mask by Hydride Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L356-L359	1.4	60
155	The formation of crystalline defects and crystal growth mechanism in In _x Ga _{1-x} N/GaN heterostructure grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 24-28	1.6	55
154	Raman Scattering Spectroscopy of Residual Stresses in Epitaxial AlN Films. <i>Applied Physics Express</i> , 2011 , 4, 031001	2.4	54
153	Fabrication of Deep-Ultraviolet-Light-Source Tube Using Si-Doped AlGaIn. <i>Applied Physics Express</i> , 2011 , 4, 042103	2.4	52
152	Formation of GaN Self-Organized Nanotips by Reactive Ion Etching. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L1301-L1304	1.4	51
151	Metalorganic vapor phase epitaxy growth of (In _x Ga _{1-x} N/GaN) _n layered structures and reduction of indium droplets. <i>Journal of Crystal Growth</i> , 1994 , 145, 209-213	1.6	50
150	MOVPE growth of GaN on a misoriented sapphire substrate. <i>Journal of Crystal Growth</i> , 1991 , 107, 509-512.	6	49
149	Metalorganic Vapor Phase Epitaxy of Thick InGaIn on Sapphire Substrate. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 3381-3384	1.4	41
148	Cross-sectional TEM study of microstructures in MOVPE GaN films grown on Al ₂ O ₃ with a buffer layer of AlN. <i>Journal of Crystal Growth</i> , 1991 , 115, 381-387	1.6	41
147	Hydride vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 67-71	1.6	39
146	The Composition Pulling Effect in InGaIn Growth on the GaN and AlGaIn Epitaxial Layers Grown by MOVPE. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 89		38
145	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaIn quantum wells. <i>Applied Physics Letters</i> , 2012 , 101, 042110	3.4	37

144	Impact of high-temperature annealing of AlN layer on sapphire and its thermodynamic principle. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FL02	1.4	36
143	MOVPE growth of thick homogeneous InGaN directly on sapphire substrate using AlN buffer layer. <i>Solid-State Electronics</i> , 1997 , 41, 145-147	1.7	36
142	Effect of thermal annealing on AlN films grown on sputtered AlN templates by metalorganic vapor phase epitaxy. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 01AD05	1.4	35
141	Growth of Thick AlN Layer by Hydride Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, L505-L507	1.4	35
140	Selective Area Growth of GaN Using Tungsten Mask by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, L845-L848	1.4	35
139	A study on barrier height of Au _x Al _x Ga _{1-x} N Schottky diodes in the range 0 ≤ x ≤ 0.20. <i>Solid-State Electronics</i> , 1997 , 41, 287-294	1.7	32
138	The initial stage of LPE growth of InGaAsP on GaAs in the region of immiscibility. <i>Journal of Crystal Growth</i> , 1986 , 79, 978-983	1.6	29
137	Transmission Electron Microscopy Investigation of Dislocations in GaN Layer Grown by Facet-Controlled Epitaxial Lateral Overgrowth. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L309-L312	1.4	24
136	Growth and Characterization of AlGaIn Multiple Quantum Wells for Electron-Beam Target for Deep-Ultraviolet Light Sources. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 01AF03	1.4	23
135	High-quality AlN growth on 6H-SiC substrate using three dimensional nucleation by low-pressure hydride vapor phase epitaxy. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FL03	1.4	22
134	Sub-micron fine structure of GaN by metalorganic vapor phase epitaxy (MOVPE) selective area growth (SAG) and buried structure by epitaxial lateral overgrowth (ELO). <i>Journal of Crystal Growth</i> , 1998 , 189-190, 78-82	1.6	20
133	Inhomogeneous distribution of defect-related emission in Si-doped AlGaIn epitaxial layers with different Al content and Si concentration. <i>Journal of Applied Physics</i> , 2014 , 115, 053509	2.5	19
132	Photoluminescence study of Si-doped a-plane GaN grown by MOVPE. <i>Journal of Crystal Growth</i> , 2009 , 311, 2906-2909	1.6	19
131	Nitriding r-plane sapphire to improve crystal qualities and surface morphologies of a-plane GaN grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2009 , 95, 121910	3.4	19
130	Structural and electrical properties of Si-doped a-plane GaN grown on r-plane sapphire by MOVPE. <i>Journal of Crystal Growth</i> , 2009 , 311, 2899-2902	1.6	18
129	Effects of initial stages on the crystal quality of nonpolar a-plane AlN on r-plane sapphire by low-pressure HVPE. <i>Journal of Crystal Growth</i> , 2009 , 311, 3801-3805	1.6	18
128	Crystal Orientation Fluctuation of Epitaxial-Lateral-Overgrown GaN with W Mask and SiO ₂ Mask Observed by Transmission Electron Diffraction and X-Ray Rocking Curves. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L1299-L1302	1.4	18
127	Influence of off-cut angle of r-plane sapphire on the crystal quality of nonpolar a-plane AlN by LP-HVPE. <i>Journal of Crystal Growth</i> , 2009 , 311, 4473-4477	1.6	17

126	Selective area growth and epitaxial lateral overgrowth of GaN by metalorganic vapor phase epitaxy and hydride vapor phase epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 59, 104-111	3.1	17
125	Fabrication of high-crystallinity a-plane AlN films grown on r-plane sapphire substrates by modulating buffer-layer growth temperature and thermal annealing conditions. <i>Journal of Crystal Growth</i> , 2017 , 468, 845-850	1.6	16
124	Control of AlN buffer/sapphire substrate interface for AlN growth. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2069-2071		16
123	Effects of Substrate Plane on the Growth of High Quality AlN by Hydride Vapor Phase Epitaxy. <i>Applied Physics Express</i> , 2009 , 2, 111004	2.4	16
122	Facets Formation Mechanism of GaN Hexagonal Pyramids on Dot-Patterns via Selective MOVPE. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 395, 267		16
121	LPE Growth and Surface Morphology of In _x Ga _{1-x} As _y P _{1-y} (y \leq 0.01) on (100) GaAs. <i>Japanese Journal of Applied Physics</i> , 1984 , 23, 68-73	1.4	16
120	MOVPE growth of GaN on Si substrate with 3C-SiC buffer layer. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FL09	1.4	14
119	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. <i>Journal of Crystal Growth</i> , 2012 , 350, 69-71	1.6	14
118	Silicon concentration dependence of optical polarization in AlGa _n epitaxial layers. <i>Applied Physics Letters</i> , 2011 , 98, 021910	3.4	14
117	Influence of growth interruption and Si doping on the structural and optical properties of Al _x GaN/AlN (x $>$ 0.5) multiple quantum wells. <i>Journal of Crystal Growth</i> , 2007 , 298, 500-503	1.6	14
116	Suppression of Crack Generation Using High-Compressive-Strain AlN/Sapphire Template for Hydride Vapor Phase Epitaxy of Thick AlN Film. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, L552-L555	1.4	14
115	Extraordinary Optical Transmission Exhibited by Surface Plasmon Polaritons in a Double-Layer Wire Grid Polarizer. <i>Plasmonics</i> , 2015 , 10, 1657-1662	2.4	13
114	Growth of High-Quality Si-Doped AlGa _n by Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 095502	1.4	13
113	Influence of growth conditions on Al incorporation to Al _x Ga _{1-x} N (x $>$ 0.4) grown by MOVPE. <i>Journal of Crystal Growth</i> , 2007 , 298, 372-374	1.6	13
112	Effects of carrier gas ratio and growth temperature on MOVPE growth of AlN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 499-502		12
111	Characterization of GaN-Based Schottky Barrier Ultraviolet (UV) Detectors in the UV and Vacuum Ultraviolet (VUV) Region Using Synchrotron Radiation. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L368-L370	1.4	12
110	Antireflection Effect of Self-Organized GaN Nanotip Structure from Ultraviolet to Visible Region. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, L1134-L1136	1.4	12
109	Raman Scattering of InGaAsP Lattice-Matched to GaAs in the Region of Immiscibility. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 2718-2721	1.4	11

108	Cathodoluminescence of MOVPE-grown GaN layer on Al_2O_3 . <i>Journal of Crystal Growth</i> , 1990 , 99, 375-380	11
107	Orientation dependence of polarized Raman spectroscopy for nonpolar, semi-polar, and polar bulk GaN substrates. <i>Applied Physics Letters</i> , 2012 , 100, 011909	3-4 10
106	AlN Grown on a- and n-Plane Sapphire Substrates by Low-Pressure Hydride Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JB31	1.4 10
105	Metalorganic Vapor Phase Epitaxy Growth and Study of Stress in AlGa _N Using Epitaxial AlN as Underlying Layer. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L572-L574	1.4 10
104	Epitaxial lateral overgrowth of GaN on selected-area Si(1 1 1) substrate with nitrided Si mask. <i>Journal of Crystal Growth</i> , 2003 , 248, 573-577	1.6 10
103	Gradual tilting of crystallographic orientation and configuration of dislocations in GaN selectively grown by vapour phase epitaxy methods. <i>Journal of Electron Microscopy</i> , 2000 , 49, 331-8	10
102	Growth of High-Quality Si-Doped AlGa _N by Low-Pressure Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 095502	1.4 10
101	HVPE growth of AlN on trench-patterned 6H-SiC substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 467-469	9
100	Deep Electronic Levels of Al _x Ga _{1-x} N with a Wide Range of Al Composition Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 101001	1.4 9
99	Optical properties of MOVPE-grown a-plane GaN and AlGa _N . <i>Journal of Crystal Growth</i> , 2009 , 311, 2903-2905	9
98	Blue emission from InGa _N /GaN hexagonal pyramid structures. <i>Superlattices and Microstructures</i> , 2007 , 41, 341-346	2.8 9
97	Analysis of Compositional Variation at Initial Transient Time in LPE Growth of InGaAsP/GaAs System. <i>Japanese Journal of Applied Physics</i> , 1985 , 24, 1030-1035	1.4 9
96	Using surface-plasmon polariton at the GaP-Au interface in order to detect chemical species in high-refractive-index media. <i>Optics Communications</i> , 2015 , 341, 64-68	2 8
95	Electron microscopy analysis of microstructure of postannealed aluminum nitride template. <i>Applied Physics Express</i> , 2016 , 9, 065502	2.4 8
94	Correlation between in-plane strain and optical polarization of Si-doped AlGa _N epitaxial layers as a function of Al content and Si concentration. <i>Journal of Applied Physics</i> , 2012 , 112, 033512	2.5 8
93	Fabrication of Binary Diffractive Lenses and the Application to LED Lighting for Controlling Luminosity Distribution. <i>Optics and Photonics Journal</i> , 2013 , 03, 67-73	0.3 8
92	Huge binding energy of localized biexcitons in Al-rich Al _x Ga _{1-x} N ternary alloys. <i>Applied Physics Letters</i> , 2011 , 98, 081907	3-4 8
91	Photoluminescence due to Inelastic Biexciton Scattering from an Al _{0.61} Ga _{0.39} N Ternary Alloy Epitaxial Layer at Room Temperature. <i>Applied Physics Express</i> , 2012 , 5, 072401	2.4 8

90	In Situ Monitoring of GaN Reactive Ion Etching by Optical Emission Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L313-L315	1.4	8
89	Growth of InGaP epitaxial layers by liquid phase electro-epitaxy. <i>Journal of Crystal Growth</i> , 1991 , 115, 304-308	1.6	8
88	Effect of lattice mismatch between epitaxial layer and substrate on immiscibility of InGaAsP/GaAs LPE layers. <i>Journal of Crystal Growth</i> , 1988 , 87, 446-452	1.6	8
87	Effects of AlN buffer layer thickness on the crystallinity and surface morphology of 10- μ m-thick a-plane AlN films grown on-plane sapphire substrates. <i>Applied Physics Express</i> , 2016 , 9, 081001	2.4	8
86	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al _{0.60} Ga _{0.40} N/Al _{0.70} Ga _{0.30} N multiple quantum wells. <i>Applied Physics Express</i> , 2017 , 10, 021002	2.4	7
85	Selective-area growth of GaN on non- and semi-polar bulk GaN substrates. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FL04	1.4	7
84	Binding energy of localized biexcitons in AlGaIn-based quantum wells. <i>Applied Physics Express</i> , 2014 , 7, 122101	2.4	7
83	Fabrication of crack-free thick AlN film on a-plane sapphire by low-pressure HVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 576-579		7
82	HVPE growth of thick AlN on trench-patterned substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1483-1486		7
81	In-plane electric field induced by polarization and lateral photovoltaic effect in a-plane GaN. <i>Applied Physics Letters</i> , 2009 , 94, 231102	3.4	7
80	In-plane structural anisotropy and polarized Raman-active mode studies of nonpolar AlN grown on 6H-SiC by low-pressure hydride vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2010 , 312, 490-494	1.6	7
79	Microstructural analysis of an epitaxial AlN thick film/trench-patterned template by three-dimensional reciprocal lattice space mapping technique. <i>Applied Physics Express</i> , 2016 , 9, 111001	2.4	6
78	Realization of Maskless Epitaxial Lateral Overgrowth of GaN on 3C-SiC/Si Substrates. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JB07	1.4	6
77	HVPE growth of c-plane AlN on a-plane sapphire using nitridation layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 470-472		6
76	Fabrication of a binary diffractive lens for controlling the luminous intensity distribution of LED light. <i>Optical Review</i> , 2009 , 16, 455-457	0.9	6
75	Characterization of GaN based Schottky UV detectors in the vacuum UV (VUV) and the soft X-ray (SX) region (10 μ m-100 nm). <i>Physica Status Solidi A</i> , 2003 , 200, 147-150		6
74	LPE growth of InGaP/InGaAsP multiple thin layers on (111)A GaAs substrates. <i>Journal of Crystal Growth</i> , 1989 , 98, 653-658	1.6	6
73	Excitation mechanism of surface plasmon polaritons in a double-layer wire grid structure. <i>Applied Physics A: Materials Science and Processing</i> , 2017 , 123, 1	2.6	5

72	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 765-768	1.6	5
71	Selective Area Growth of Semipolar (202 1) and (202 1) GaN Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JC06	1.4	5
70	Observation of longitudinal-optic-phonon-plasmon-coupled mode in n-type AlGa _N alloy films. <i>Applied Physics Letters</i> , 2011 , 99, 251904	3.4	5
69	Recombination dynamics of localized excitons in Al _x Ga _{1-x} N (0.37). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2133-2135		5
68	Variation of Surface Potentials of Si-Doped Al _x Ga _{1-x} N (0. <i>Applied Physics Express</i> , 2010 , 3, 021004	2.4	5
67	Study of High-Quality and Crack-Free GaN Growth on 3C-SiC/Separation by Implanted Oxygen (111). <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 041001	1.4	5
66	Effects of initial conditions and growth temperature on the properties of nonpolar a -plane AlN grown by LP-HVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S478-S481		5
65	a -plane AlN and AlGa _N growth on r -plane sapphire by MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2107-2110		5
64	Fabrication of thick AlN film by low pressure hydride vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1479-1482		5
63	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN Via Metalorganic Vapor-Phase Epitaxy (MOVPE). <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		5
62	Characterization of Interface Instability in InGaAsP LPE Growth on GaAs by Fourier Analysis. <i>Japanese Journal of Applied Physics</i> , 1985 , 24, 822-827	1.4	5
61	Study on the effects of AlN interlayer in thick GaN grown on 3C-SiC/Si substrates. <i>Journal of Crystal Growth</i> , 2013 , 370, 254-258	1.6	4
60	Si concentration dependence of structural inhomogeneities in Si-doped Al _x Ga _{1-x} N/Al _y Ga _{1-y} N multiple quantum well structures (x = 0.6) and its relationship with internal quantum efficiency. <i>Journal of Applied Physics</i> , 2014 , 116, 235703	2.5	4
59	Cathodoluminescence Study of Optical Inhomogeneity in Si-Doped AlGa _N Epitaxial Layers Grown by Low-Pressure Metalorganic Vapor-Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JL074	1.4	4
58	Evidence for moving of threading dislocations during the VPE growth in GaN thin layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1487-1490		4
57	n-type conductivity control of AlGa _N with high Al mole fraction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1435-1438		4
56	Influence of Si doping on the optical and structural properties of InGa _N films. <i>Journal of Crystal Growth</i> , 2006 , 290, 374-378	1.6	4
55	Growth control of carbon nanotubes by plasma-enhanced chemical vapor deposition and reactive ion etching. <i>Vacuum</i> , 2006 , 80, 798-801	3.7	4

54	Characterization of high-quality epitaxial AlN films grown by MOVPE. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 693, 774		4
53	HVPE homoepitaxy on freestanding AlN substrate with trench pattern. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 334-337		3
52	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al _{0.61} Ga _{0.39} N Epitaxial Layer. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700374	1.3	3
51	Effect of surface pretreatment of r-plane sapphire substrates on the crystal quality of a-plane AlN. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FA12	1.4	3
50	Excitation-dependent carrier dynamics in Al-rich AlGa _N layers and multiple quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 1043-1049	1.3	3
49	Anisotropic crystalline morphology of epitaxial thick AlN films grown on triangular-striped AlN/sapphire template. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 731-735	1.6	3
48	Effects of Si doping in high-quality AlN grown by MOVPE on trench-patterned template. <i>Journal of Crystal Growth</i> , 2013 , 370, 74-77	1.6	3
47	Enhanced emission efficiency of InGa _N films with Si doping. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1944-1948		3
46	TEM Analysis of Threading Dislocations in ELO-GaN Grown with Controlled Facet Planes. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 639, 11591		3
45	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN VIA Metalorganic Vapor-Phase Epitaxy (MOVPE). <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999 , 4, 118-123		3
44	A verification of immiscibility in InGaAsP quaternary alloys. <i>Journal of Crystal Growth</i> , 1988 , 92, 311-315	1.6	3
43	Confinement-enhanced biexciton binding energy in AlGa _N -based quantum wells. <i>Applied Physics Express</i> , 2017 , 10, 051003	2.4	2
42	Enhancement of blue emission from Mg-doped GaN activated at low temperature in O ₂ /N ₂ mixture. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2750-2753		2
41	Reduction of dislocation density in AlGa _N with high AlN molar fraction by using a rugged AlN epilayer. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 831, 353		2
40	Effects of buffer layers and advanced technologies on heteroepitaxy of GaN 2001 , 210-232		2
39	Selective Area Growth (SAG) and Epitaxial Lateral Overgrowth (ELO) of GaN Using Tungsten Mask. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		2
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